

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC2290

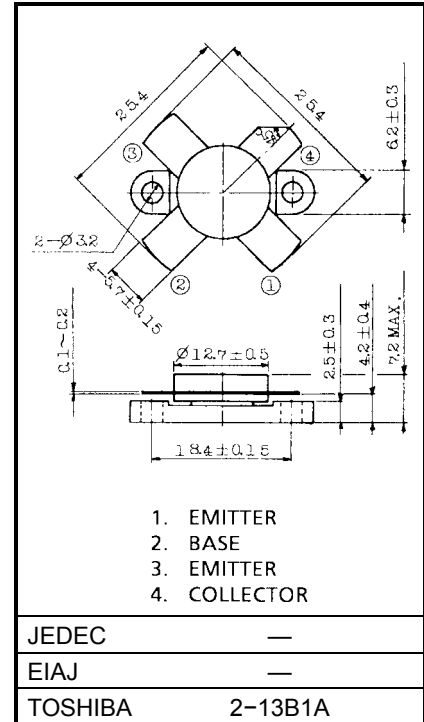
2~30MHz SSB LINEAR POWER AMPLIFIER APPLICATIONS
(LOW SUPPLY VOLTAGE USE)

Unit in mm

- Specified 12.5V, 28MHz Characteristics
- Output Power : $P_o = 60W_{PEP}$ (Min.)
- Power Gain : $G_p = 11.8dB$ (Min.)
- Collector Efficiency : $\eta_C = 35\%$ (Min.)
- Intermodulation Distortion: $IMD = -30dB$ (Max.)

MAXIMUM RATINGS ($T_c = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	45	V
Collector-Emitter Voltage	V_{CES}	45	V
Collector-Emitter Voltage	V_{CEO}	18	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	20	A
Collector Power Dissipation	P_C	175	W
Junction Temperature	T_j	175	$^\circ C$
Storage Temperature Range	T_{stg}	-65~175	$^\circ C$



Weight: 5.2g

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ELECTRICAL CHARACTERISTICS (T_c = 25°C)

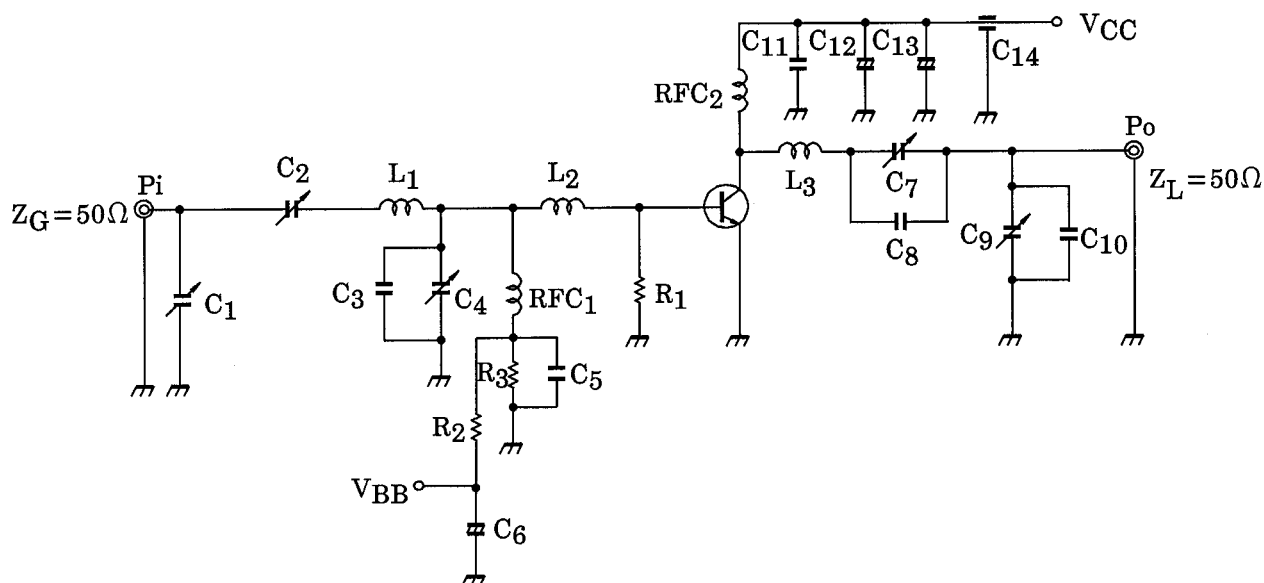
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C = 100mA, I _B = 0	18	—	—	V
Collector-Emitter Breakdown Voltage	V _(BR) CES	I _C = 100mA, V _{EB} = 0	45	—	—	V
Emitter-Base Breakdown Voltage	V _(BR) EBO	I _E = 1mA, I _C = 0	4	—	—	V
DC Current Gain	h _{FE}	V _{CE} = 5V, I _C = 10A *	10	—	150	—
Collector Output Capacitance	C _{ob}	V _{CB} = 12.5V, I _E = 0 f = 1MHz	—	—	500	pF
Power Gain	G _p	V _{CC} = 12.5V, f ₁ = 28.000MHz, f ₂ = 28.001MHz I _{idle} = 50mA P _o = 60W _{PEP} (Fig.)	11.8	13.8	—	dB
Input Power	P _i		—	2.5	4	W _{PEP}
Collector Efficiency	η _C		35	—	—	%
Intermodulation Distortion	IMD		—	—	-30	dB
Series Equivalent Input Impedance	Z _{in}	V _{CC} = 12.5V, f ₁ = 28.000MHz, f ₂ = 28.001MHz P _o = 60W _{PEP}	—	1.02 -j0.17	—	Ω
Series Equivalent Output Impedance	Z _{out}		—	0.86 -j0.21	—	Ω

* Pulse Test: Pulse Width ≤ 100μs, Duty Cycle ≤ 3%

CAUTION

Beryllia Ceramics is used in this product. The dust or vapor can be dangerous to humans. Do not break, cut, crush or dissolve chemically. Dispose of this product properly according to law. Do not intermingle with normal industrial or domestic waste.

Fig. Pi TEST CIRCUIT



C₁, C₂, C₄, C₇ : 7~150pF

C₃ : 250pF

C₅ : 0.4μF

C₆ : 100μF 10WV

C₈ : 150pF

C₉ : 10~200pF

C₁₀ : 600pF

C₁₁ : 0.4μF

C₁₂, C₁₃ : 22μF 35WV

C₁₄ : 1000pF

(FEED THROUGH)

L₁ : φ0.8 ENAMEL COATED COPPER WIRE, 9ID, 6T

L₂ : φ1 SILVER PLATED COPPER WIRE, 9ID, 2T

L₃ : φ1.5 ENAMEL COATED COPPER WIRE, 9ID, 5T

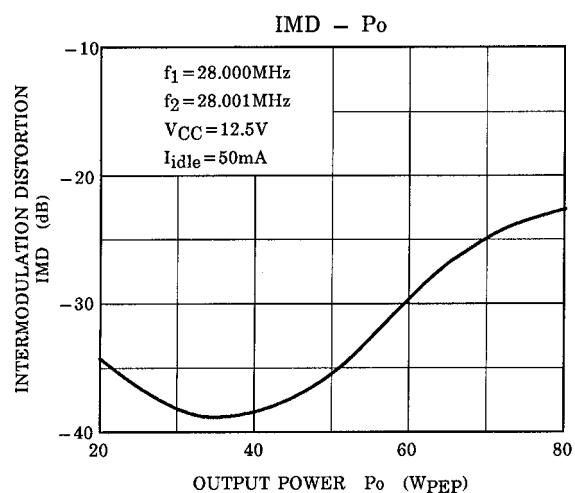
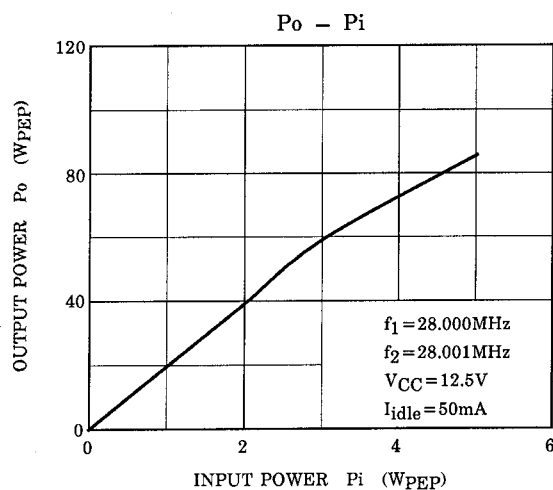
RFC₁ : φ0.8 ENAMEL COATED COPPER WIRE, 9ID, 20T

RFC₂ : φ1.5 ENAMEL COATED COPPER WIRE, 12ID, 15T

R₁ : 5.6Ω (1/2W)

R₂ : 5Ω (5W)

R₃ : 1.5Ω (10W)



CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.